

Amendments to the Claims:

Please amend claim 42. The claims are as follows:

1-20 (Canceled)

21. (Previously Presented) An electrical structure, comprising:

a parent terrain denoted as  $V_0$ ; and

voltage islands denoted as  $V_1$  and  $V_2$ , said voltage island  $V_1$  nested within said parent terrain  $V_0$  and said voltage island  $V_2$  nested within said voltage island  $V_1$ .

22. (Previously Presented) The electrical structure of claim 41, wherein each voltage island of the  $N$  voltage islands includes one or more voltage power supplies selected from the group consisting of an internal voltage island VDDI power supply, an externally supplied state saving VDDSS power supply, an externally supplied VDDN power supply, and combinations thereof.

23. (Previously Presented) The electrical structure of claim 22, wherein said one or more power supplies of voltage island  $V_X$  for  $X=1, 2, \dots, N$  are each independently coupled to one of (a) said one or more power supplies of voltage island  $V_Y$ , for  $Y=1, 2, \dots, N$ ,  $X$  not equal to  $Y$ , (b) a VDDO power supply of said parent terrain or (c) one or more external to said parent terrain power supplies.

24. (Previously Presented) The electrical structure of claim 41, wherein each voltage island of the  $N$  voltage islands includes (a) an externally supplied VDDN power supply and a voltage shifting means, or (b) said externally supplied VDDN power supply and a fencing means, or (c)

said externally supplied VDDN power supply, said voltage shifting means and said fencing means.

25. (Previously Presented) The electrical structure of claim 24, wherein said fencing means comprises logic latches.

26. (Previously Presented) The electrical structure of claim 24, wherein each voltage island of the N voltage islands further includes one or more substructures selected from the group consisting of (a) an internal voltage island VDDI power distribution network, (b) state saving means, (c) one or more switching elements coupled between said externally supplied VDDN power supply and said internal voltage island VDDI power distribution network, and (d) one or more voltage buffering circuits.

27. (Previously Presented) The electrical structure of claim 26, wherein said one or more switching elements is selected from the group consisting of hard connections, voltage regulators, headers and footers.

28. (Previously Presented) The electrical structure of claim 26, wherein said state saving means includes at least one state saving latch.

29. (Previously Presented) The electrical structure of claim 41, wherein one or more voltage islands of the N voltage islands further includes a power management state machine coupled to an internal voltage island VDDI power supply distribution network, said power management

state machine of voltage island  $V_X$  for  $X=1, 2, \dots, N$  located in (a) voltage island  $V_Y$  for  $Y=1, 2, \dots, N$ ,  $Y$  less than  $X$ , or (b) in said parent terrain.

30. (Previously Presented) The electrical structure of claim 21, wherein said parent terrain is an integrated circuit chip or a voltage island within said integrated circuit chip.

31. (Previously Presented) A method, comprising:

providing a parent terrain denoted as  $V_0$ ; and

nesting a voltage island  $V_1$  within said parent terrain  $V_0$  and nesting a voltage island  $V_2$  within said voltage island  $V_1$ .

32. (Previously Presented) The method of claim 42, wherein each voltage island of the  $N$  voltage islands includes one or more voltage power supplies selected from the group consisting of an internal voltage island  $VDDI$  power supply, an externally supplied state saving  $VDDSS$  power supply, an externally supplied  $VDDN$  power supply, and combinations thereof.

33. (Previously Presented) The electrical structure of claim 42, wherein said one or more power supplies of voltage island  $V_X$  for  $X=1, 2, \dots, N$  are each independently coupled to one of (a) said one or more power supplies of voltage island  $V_Y$ , for  $Y=1, 2, \dots, N$ ,  $X$  not equal to  $Y$ , (b) a  $VDDO$  power supply of said parent terrain or (c) one or more external to said parent terrain power supplies.

34. (Previously Presented) The method of claim 31, wherein each voltage island of the N voltage islands includes (a) an externally supplied VDDN power supply and a voltage shifting means, or (b) said externally supplied VDDN power supply and a fencing means, or (c) said externally supplied VDDN power supply, said voltage shifting means and said fencing means.
35. (Previously Presented) The method of claim 34, wherein said fencing means comprises logic latches.
36. (Previously Presented) The method of claim 34, wherein each voltage island of the N voltage islands further includes one or more substructures selected from the group consisting of (a) an internal voltage island VDDI power distribution network, (b) state saving means, (c) one or more switching elements coupled between said externally supplied VDDN power supply and said internal voltage island VDDI power distribution network, and (d) one or more voltage buffering circuits.
37. (Previously Presented) The method of claim 36, wherein said one or more switching elements is selected from the group consisting of hard connections, voltage regulators, headers and footers.
38. (Previously Presented) The method of claim 36, wherein said state saving means includes at least one state saving latch.

39. (Previously Presented) The electrical structure of claim 42, wherein one or more voltage islands of the  $N$  voltage islands further includes a power management state machine coupled to an internal voltage island VDDI power supply distribution network, said power management state machine of voltage island  $V_X$  for  $X=1, 2, \dots, N$  located in (a) a voltage island  $V_Y$  for  $Y=1, 2, \dots, N$ ,  $Y$  less than  $X$ , or (b) in said parent terrain.

40. (Previously Presented) The method of claim 31, wherein said parent terrain is an integrated circuit chip or a voltage island within said integrated circuit chip.

41. (Previously Presented) The electrical structure of claim 21, further including:

additional voltage islands denoted as  $V_3, V_4, \dots, V_N$ , a voltage island  $V_Z$  nested within a voltage island  $V_{Z-1}$  for  $Z=3, 4, \dots, N$ , wherein  $N$  is an integer of at least 3.

42. (Currently Amended) The method of claim ~~[[21]]~~ 31, further including:

providing additional voltage islands denoted as  $V_3, V_4, \dots, V_N$ ; and

nesting a voltage island  $V_Z$  within a voltage island  $V_{Z-1}$  for  $Z=3, 4, \dots, N$ , wherein  $N$  is an integer of at least 3.